

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (original) A method comprising:
defining a pair of spaced apart floating gates over a substrate;
forming a stacked control gate over each floating gate; and
forming a drain and a pair of sources by implantation using said stacked control gates as a mask.
2. (original) The method of claim 1 including using said control gates to protect said floating gates from said implantation.
3. (original) The method of claim 1 including self aligning said sources and drain to both of said control gates.
4. (original) The method of claim 1 including using substrate hot electron injection to charge said floating gates.
5. (new) The method of claim 1, wherein defining a pair of spaced apart floating gates over a substrate includes,
forming the spaced apart floating gates over a triple well defined within the substrate.

6. (new) The method of claim 1, wherein the pair of spaced apart floating gates are composed of polysilicon.

7. (new) The method of claim 1, wherein the control gate is composed of polysilicon.

8. (new) The method of claim 1, wherein the drain and the pair of sources are formed contemporaneously.